

Publications

International Journals:

1. Yeasir Arafat , Farseem M. Mohammedy , M. M. Shahidul Hassan, "Optical and Other Measurement Techniques of Carrier Lifetime in Semiconductors," International Journal of Optoelectronic Engineering, Vol. 2, No. 2, pp. 5-11, 2012
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3. M M Shahidul Hassan and Orchi Hassan, "Minority Carrier Profile and Storage Time of a Nonuniformly Doped n-Si Schottky Barrier Diode," Journal of Electron Devices, Vol. 11, pp. 609-615, 2011.
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7. M. M. Shahidul Hassan, Touhidur Rahman and Md. Ziaur Rahman Khan, "Analytical model for base transit time of a bipolar transistor with Gaussian doped base," Solid-State Electron.,Vol. 50, No. 3, pp. 327-332 , 2006.
8. Md. Anwarul Abedin and Dr. M. M. Shahidul Hassan, "Base Transit Time Model of a Bipolar Junction Transistor Considering Kirk Effect," Journal of The Institution of Engineers, Singapore, Vol. 45, Issue 5, 2005.
9. Md. Anwarul, Abedin and M. M., Shahidul Hassan, Analytical base transit time model of uniformly doped base bipolar transistors considering Kirk effect, The Journal of the Institution of Engineers, Malaysia, vol. 66(3), 2005, pages 42-46
10. Md. Z. R. and M.M.S. Hassan and T.Rahman and A. k. M. Ahsan, "Expression for Base Transit Time in Bipolar Transistors," Int. J. Electronics, Vol. 92, No. 4, pp. 215-229, April 2005.
11. M. M. Shahidul Hassan , A. H. M. A. Rahim , "Induced Base Transit Time of an Epitaxial $n^+pn^-n^+$ Bipolar Transistor in Saturation," Solid-State Electronics,Vol. 47, No.6, pp. 943-950, 2003.
12. M. M. Shahidul Hassan, "Base Transit Time of an Epitaxial $n^+pn^-n^+$ Bipolar Transistor Considering Kirk Effect," Int. J. Microelectronics and Reliability, Vol. 43, No. 2, pp. 327-332, 2003.
13. M. M. Shahidul Hassan and S. Hasibul Majid, "Electrical Characteristics of an Epitaxial Schottky Barrier Diode," International Journal of Electronics, Vol. 88, No. 9, pp. 957-967, 2001.
14. M. M. Shahidul Hassan and A. H. Khondoker, "New Expression for Base Transit Time in a Bipolar Transistor for all levels of Injection," Microelectronics and

- Reliability, Vol. 41, No. 1, pp. 137-140, 2001.
15. M. M. Shahidul Hassan, "Analytical Base Transit Time of Integrated Bipolar Transistors in Quasi-saturation and Hard-saturation," IEE Proc.-Circuits, Devices and Systems, 147, No. 2, pp. 129-132, 2000.
 16. M. M. Shahidul Hassan, "Characteristics of Epitaxial Schottky Barrier Diode for all Levels of Injection," Solid-State Electronics, Vol. 44, No. 6, pp.1111-1116, 2000.
 17. M. M. Shahidul Hassan, "Modelling of Lightly Doped Collector of a Bipolar Transistor Operating in Quasi-saturation Region," Int. Journal of Electronics, Vol.86, No.1, pp. 1-14, 1999.
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 19. M. M. Shahidul Hassan and Md. Aynal Haque, "Evaluation of Optimal Collector Parameters of a Transistor with Burried Layer," Int. J. Electronics, Vol. 75, No. 3, pp. 437-440, 1993.
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 25. M. M. Shahidul Hassan and H. Domingos, "Control of Current Mode Second Breakdown in Transistors through Use of Double-Graded Collectors," Solid-State Electronics, Vol. 33, No. 10, pp. 1217-1221, 1991.
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2. M M Shahidul Hassan, Orchi Hassan and Md. Azharul Haque, “Minority Carrier Profile and Storage Time of a Schottky Barrier Diode for All levels of injection,” JIEB, Vol 37, No 2, pp. 15-21, 2011.
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4. M. M. Shahidul Hassan and M. Azharul Haque, “Base Transit Time of a High Speed NPN Transistor Considering Hole current,” JIEB, Vol. EE 33, No. 1& II, pp. 120-124, Decber 2006.
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6. Md. Aynal Haque and M. M. Shahidul Hassan, “Design of a Graded Collector of High Voltage Bipolar Transistors,” JIEB, Vol. EE 27, No. 1, pp. 57-61, 1999.
7. Mohammad Zahangir Kabir and M. M. Shahidul Hassan, “Determination of Excited Energy States of Submicron Inversion MOSFETs by Variational Method,” JIEB, Vol. EE24, pp. 61-67, 1996.
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2. Md. Imran Momtaz and M. M. Shahidul Hassan, "Analytical expression for storage time and injection ratio of a non-uniformly doped n-Si SBD," International Conference on Devices, Circuits and Systems (ICDCS – 2012), Karuny University, Coimbatore, India, March 15-16, 2012.
3. Chowdhury, M. I. B. and Hassan, M. M. Shahidul, "Analytical modeling of base transit time considering recombination in the non-uniformly doped base," International Symposium on Humanities, Science & Engineering Research (SHUSER), Kuala Lumpur, Malaysia, pp. 117 - 122, June 05-07, 2011.
4. Islam, S.M.M., Arafat, Y, Chowdhury, I.B., Khan, M.Z.R. and Hassan, M.M.S., "Base transit time of a Heterojunction Bipolar Transistor with Gaussian doped Base," International Conference on Electrical and Computer Engineering (ICECE), Dhaka, Bangladesh, pp. 127 – 130, Dec. 18-20, 2010.
5. Chowdhury, M.I.B. and Hassan, M.M.S., "Analysis of base transit time for a bipolar junction transistor considering base current," International Conference on Electrical and Computer Engineering (ICECE), Dhaka, Bangladesh, pp. 20 - 24 , Dec. 18-20, 2010.
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 12. M. M. Shahidul Hassan, Md. Ziaur Rahman Khan and Touhidur Rahman, “Analytical Base Transit Time of a Bipolar Transistor Considering Field Dependent Mobility,” 3rd International Conference on Electrical & Computer Engineering, ICECE 2004, pp. 482 – 485, Dhaka, Bangladesh, 28-30 December 2004, ISBN: 984-32-1804-4.
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 20. M. M. Shahidul Hassan, A. N. Khondker and H. Domingos, “Conduction Mechanism in BJT’s during Electrical Overstress,” EOS/ESD Symposium Proc., USA, pp. 280-286, 1987.
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 23. M. M. Shahidul Hassan and H. Domingos, “The Double Graded Transistor and Its Beneficial Effect on Resistance to Current Mode Second Breakdown,” EOS/ESD Symposium Proc., USA, pp. 127-135, 1989.

Papers on Education

British Council, Sri Lanka organized a dialogue on ‘Transforming Higher Education in South Asian’ on 18-19 June 2013.

Presented a paper titled ‘Requirement of a National Framework for Overseas Higher Education Delivery Models’, parallel session 4, 18 June 2013, Cinammon Grand Hotel, Colombo 3, Srilanka.

Attended a workshop on “Regional Accreditation of Engineering Education, Qualifications and Mobility of Engineers in Asia Pacific and Africa”, 27 May 2015, Kula Lumpur, Malaysia.
Organizer: Federation of Engineering Institutions of Asia and the Pacific (FEIAP).

Published

Journal

1. M. M. Shahidul Hassan, “Revamping Higher Education in Bangladesh”, International Journal of Management and Applied Science, Vol. 2, Issue 12, Dec 2016.

Conference

1. M. M. Shahidul Hassan, “National framework for engineering education delivery models in South Asia,” International Conference on Education Social Sciences and Humanities (SOCIO-INT15), Istanbul, Turkey, 8-10 July 2015.

2. M M Shahidul Hassan,,”Challenges and Opportunities for Engineering Education in Bangladesh,” IEOM Symposium on Global Engineering Education, December 19, 2015, Dhaka, Bangladesh..

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4. M M Shahidul Hassan, “ On Challenges of Implementing Outcome Based Engineering Education in Universities in Bangladesh”, pp. 362 – 364, 20-22 Dec. 2012.

5. M. M. Shahidul Hassan, “Implementing Outcome Based Engineering Education in Bangladesh,” Advanced Education and Management [ICAEM2014], Jan 04 –Jan 06 2014, Beijing, China

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1. M. M. Shahidul Hassan, “How can we build a knowledge-based economy? ,” the Daily Star, Opinion Section, Friday, January 6, 2017.

2. M. M. Shahidul Hassan, “Global Perspectives on Higher Education in Bangladesh,” The Daily Sun, p-6, Wednesday, 8 June, 2016, <http://www.daily-sun.com/printversion/details/142418>.

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8. M. M. Shahidul Hassan, “Outcome based education: Challenges in implementation,” The Daily Sun, Saturday 12 January 2013.
9. M. M. Shahidul Hassan, Outcome based Engineering education : A paradigm shift,” The New Nation, Monday, 01 October, 2012.
10. M M. Shahidul Hassan, “Outcome-based education: Learning's new paradigm,” The Independent, 07 August 2012.
11. Professor M M Shahidul Hassan, “ Providing Quality Engineering Education,” Nation, Friday, 12 June 2009.
12. এম এম শহীদুল হাসান, “ আমেরিকার বিশ্ববিদ্যালয়ে পড়ানোর অভিজ্ঞতা,” নয়া দিগন্ত, ৪ জুলাই ২০০৯.
13. এম এম শহীদুল হাসান, “ তরুন প্রজন্মের বড় অংশ প্রকৌশল শিক্ষা নিতে আগ্রহী,” জনকণ্ঠ, বাংলাদেশ, ৩০ মার্চ ২০০৯.